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(54) MAGNETIC MEMORY ELEMENT

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a magnetic memory element and a magnetic memory array using it wherein information can be written in the memory element, the influence of the write on adjacent cells can be reduced, and a highly integrated product can be made.

SOLUTION: The magnetic memory element comprises a substrate and a magnetoresistance effect film 4 formed above the substrate, the magnetoresistance effect film 4 includes a first magnetic layer 1 and a second magnetic layer 3 separated by a nonmagnetic layer 2, and a magnetic field is applied to the first magnetic layer 1 to set the magnetizing direction of the first magnetic layer 1 to write/record information. A ferromagnetic flux control layer 6 is provided for concentrating the flux of the applied magnetic field on the first magnetic layer 1.

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